



SEMDRIVER™

Hybrid Dual IGBT Driver

SKHI 22 A / B

Preliminary Data

Absolute Maximum Ratings

Symbol	Conditions	Values	Units
V_S	Supply voltage prim.	18	V
V_{iH}	Input signal volt. (High) SKHI 22A	$V_S + 0,3$	V
SKHI 22B		5 + 0,3	V
$I_{out,PEAK}$	Output peak current	8	A
$I_{out,AVmax}$	Output average current	40	mA
f_{max}	max. switching frequency	50	kHz
V_{CE}	Collector emitter voltage sense across the IGBT	1200	V
dv/dt	Rate of rise and fall of voltage secondary to primary side	50	kV/μs
V_{isolIO}	Isolation test voltage input - output (2 sec. AC)	2500	Vac
V_{isol12}	Isolation test voltage output 1 - output 2 (2 sec. AC)	1500	V
R_{Gonmin}	Minimum rating for R_{Gon}	3	Ω
$R_{Goffmin}$	Minimum rating for R_{Goff}	3	Ω
$Q_{out/pulse}$	Max. rating for output charge per pulse	4 ¹⁾	μC
T_{op}	Operating temperature	- 40 ... + 85	°C
T_{stg}	Storage temperature	- 40 ... + 85	°C

Features

- Double driver for halfbridge IGBT modules
- SKHI 22A is compatible to old SKHI 22
- SKHI 22B has additional functionality
- CMOS compatible inputs
- Short circuit protection by V_{CE} monitoring and switch off
- Drive interlock top / bottom
- Isolation by transformers
- Supply undervoltage protection (13 V)
- Error latch / output

Typical Applications

- Driver for IGBT modules in bridge circuits in choppers, inverter drives, UPS and welding inverters

1) see fig. 6

2) At $R_{CE} = 18 \text{ k}\Omega$, $C_{CE} = 330 \text{ pF}$

Characteristics

$T_a = 25 \text{ °C}$, unless otherwise specified

Symbol	Conditions	min.	typ.	max.	Units
V_S	Supply voltage primary side	14,4	15	15,6	V
I_{SO}	Supply current primary side (no load)		80		mA
	Supply current primary side (max.)			290	mA
V_i	Input signal voltage SKHI 22A on/off SKHI 22B on/off	15 / 0 5 / 0			V
V_{IT+}	Input threshold voltage (High) SKHI 22A SKHI 22B	10,9 3,5	11,7 3,7	12,5 3,9	V
V_{IT-}	Input threshold voltage (Low) SKHI 22A SKHI 22B	4,7 1,5	5,5 1,75	6,5 2,0	V
R_{in}	Input resistance SKHI 22A SKHI 22B		10 3,3		kΩ
$V_{G(on)}$	Turn on gate voltage output		+ 15		V
$V_{G(off)}$	Turn off gate voltage output		- 7		V
R_{GE}	Internal gate-emitter resistance		22		kΩ
f_{ASIC}	Asic system switching frequency		8		MHz
$t_{d(on)IO}$	Input-output turn-on propagation time	0,85	1	1,15	μs
$t_{d(off)IO}$	Input-output turn-off propagation time	0,85	1	1,15	μs
$t_{d(err)}$	Error input-output propagation time		0,6		μs
$t_{oERRRESET}$	Error reset time		9		μs
t_{TD}	Top-Bot Interlock Dead Time SKHI 22A SKHI 22B	3,3 no interlock		4,3 4,3	μs
V_{CEsat}	Reference voltage for V_{CE} -monitoring		5 ²⁾	10	V
C_{ps}	Coupling capacitance primary secondary		12		pF
MTBF	Mean Time Between Failure $T_a = 40 \text{ °C}$		2,0		10^6 h
w	weight		45		g

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